

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88 26 April 2019 Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
- -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package:
 - Designed for smaller footprint and improved power density over older wire bond packages such as D²PAK for today's space constrained high power automotive applications
 - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
 - Increased maximum current capability and excellent current spreading
 - Improved R_{DSon}
 - Low source inductance
 - Low thermal resistance R_{th}
- LFPAK Gull Wing leads:
 - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
 - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
 - Reduced cell pitch and superjunction platform enables lower R_{DSon} in the same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs

3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- Ultra high performance power switching

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	325	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	375	W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		0.62	0.88	1	mΩ
Dynamic ch	naracteristics						
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	17	34	nC
Source-dra	in diode						
Qr	recovered charge		[2]	-	49	-	nC
S	softness factor	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	0.8	-	

[1] 325A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	S	source	0	G-UFTA)
4	S	source		mbb076 S
mb	D	mounting base; connected to drain	LFPAK88 (SOT1235)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7S1R0-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7S1R0-40H	7S1R040H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	40	V

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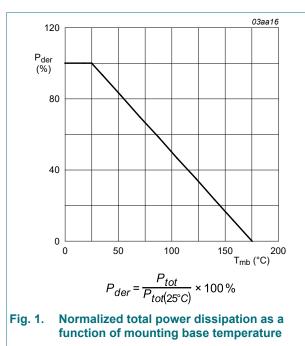
Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	375	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	325	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	1659	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C	[2]	-	350	А
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	1659	А
Avalanche rug	Igedness				-	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 120 \text{ A}; V_{sup} \leq \ 40 \text{V}; \text{R}_{GS} = 50 \Omega; \\ $	[3] [4]	-	437	mJ

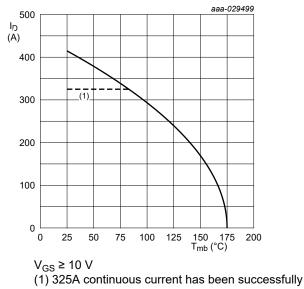
[1] 325A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[2] 350Å continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[3] single pulse avalanche rating limited by maximum junction temperature of 175°C

[4] refer to application note AN10273 for further information

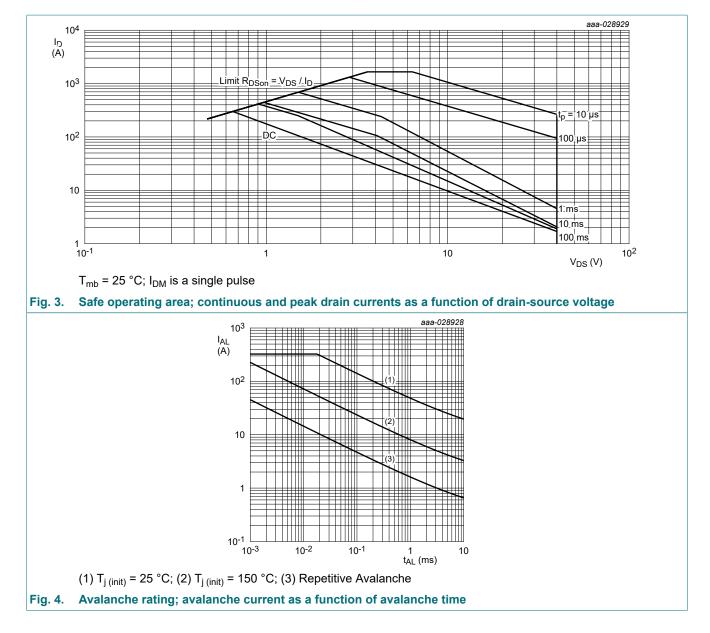




(1) 325A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88

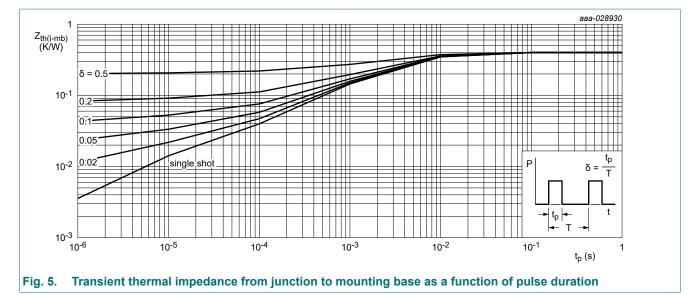


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.35	0.4	K/W

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10. Characteristics

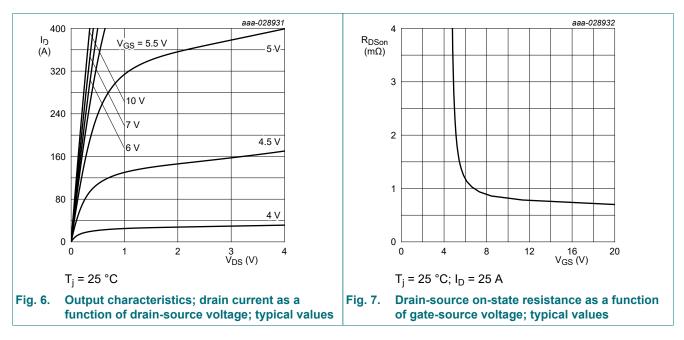
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	· · ·				
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 10</u>	1	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 10</u>	-	-	4.3	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.2	1.5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	4.7	25	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	287	1000	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	0.62	0.88	1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 12	0.87	1.3	1.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12	0.97	1.4	1.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	1.2	1.8	2.2	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.4	0.9	2.3	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	98	137	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	27	40	nC
Q _{GD}	gate-drain charge		-	17	34	nC

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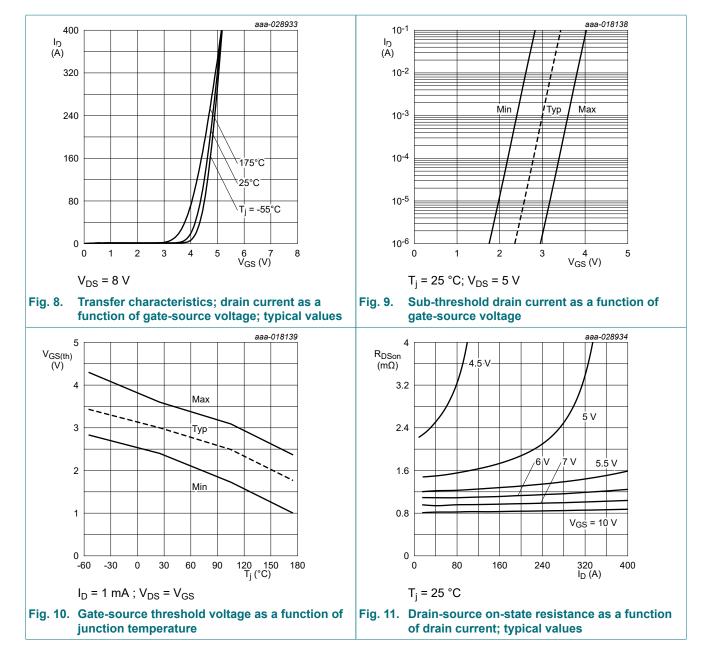
N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;		-	7373	10322	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	1578	2209	pF
C _{rss}	reverse transfer capacitance			-	295	649	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;		-	23	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	19	-	ns
t _{d(off)}	turn-off delay time			-	59	-	ns
t _f	fall time			-	26	-	ns
Source-dra	ain diode	,					
V _{SD}	source-drain voltage	V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>		-	0.76	1	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	43	-	ns
Q _r	recovered charge	V _{DS} = 20 V	[1]	-	49	-	nC
S	softness factor	I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 20 V; T _j = 25 °C		-	0.8	-	
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	0.7	-	

[1] includes capacitive recovery

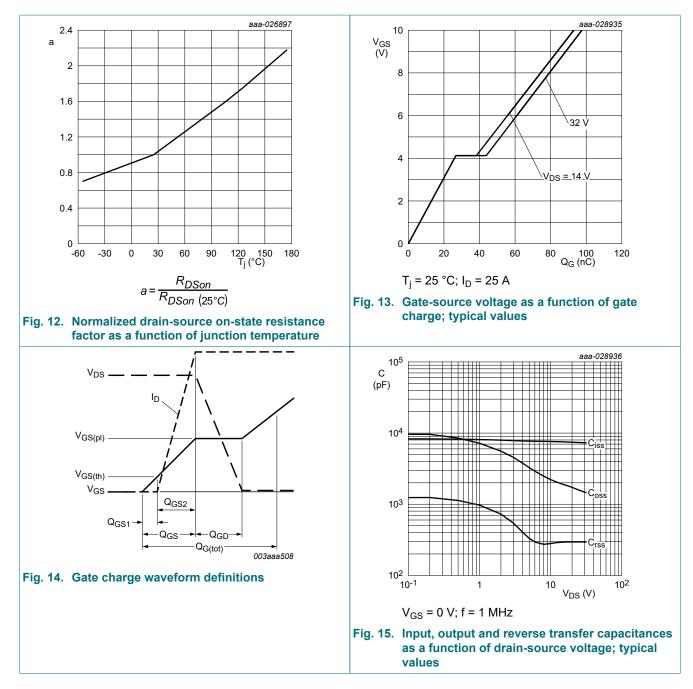


N-channel 40 V, 1.0 mQ standard level MOSFET in LFPAK88

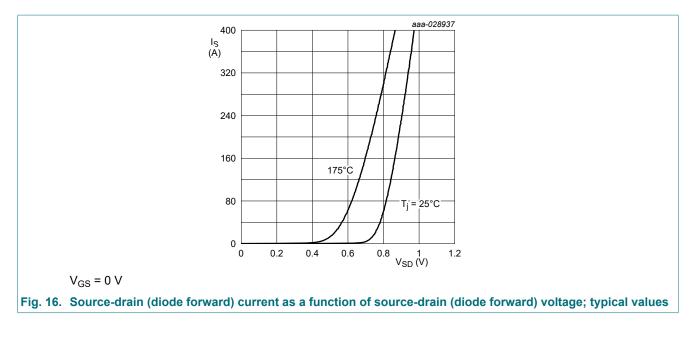


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N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88



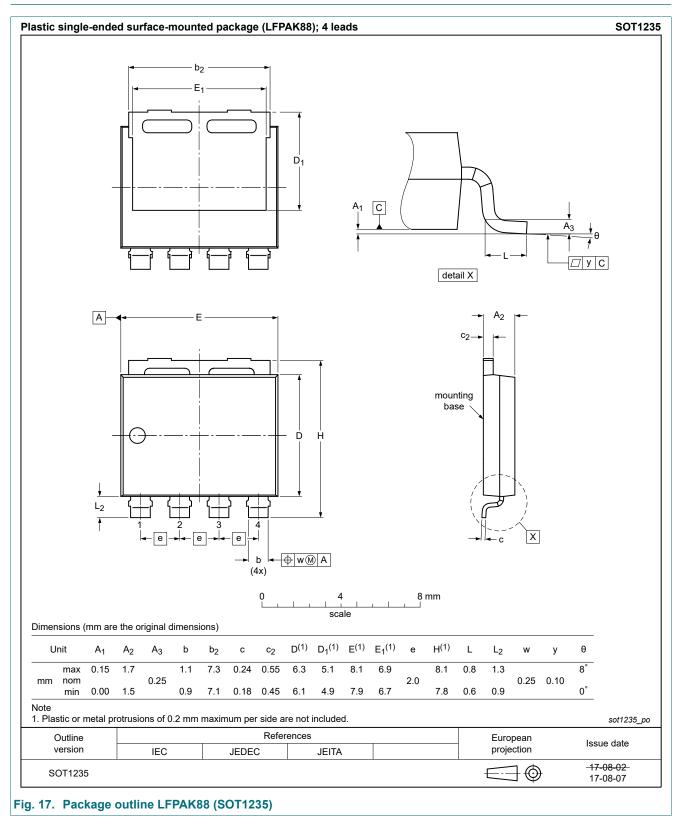
N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88



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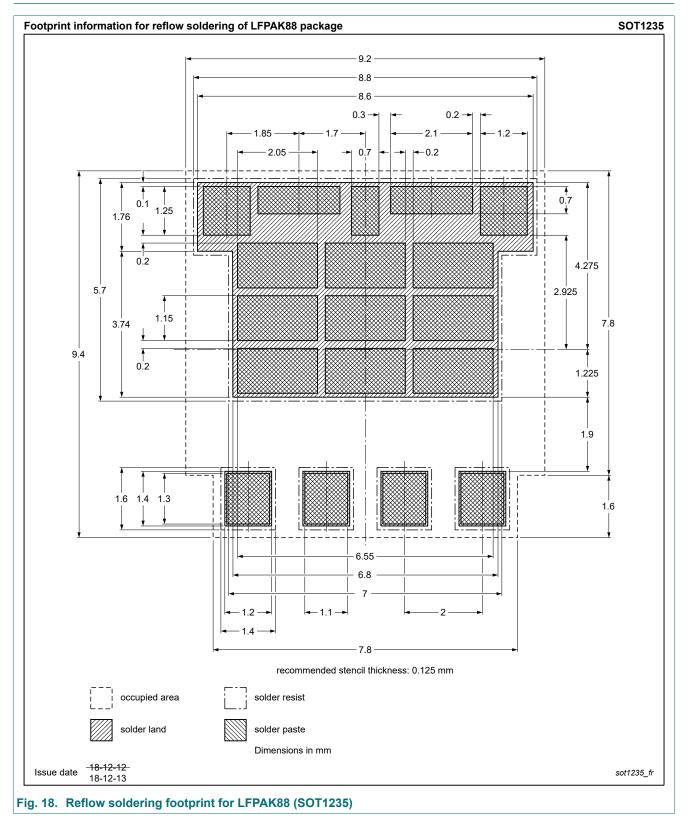
N-channel 40 V, 1.0 mQ standard level MOSFET in LFPAK88

11. Package outline



N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88

12. Soldering



N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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